



LND090A/B/C/D **Revolutionary LF-MCTs Replace MOSFETs, Bipolars & IGBTs In Switching** Apps with only 1.9nC Gate Charge

### GENERAL DESCRIPTION

Linear Dimensions introduces the revolutionary Linear Fast MCT (LF-MCT). A Linear Dimensions proprietary MCT construction (PATENTS PENDING) allows LF-MCTs for the first time to be used in fast switching applications where MOSFETs, bipolars & IGBTs are more commonly used.

LF-MCTs represent the highest current density of any switching pass element. In the past MCTs have had switching times in the 800ns+ range and been focused on high current applications. Linear Dimensions brings LF-MCTs to high frequency offline AC/DC and DC/DC switching applications with turn on times of <30ns and turn off times of <200ns (600V devices).

In AC/DC offline applications such as offline flyback converters or switching LED drivers, LF-MCTs require 1/3 the drive current of the MOSFETs typically used. Additionally, LF-MCTs require 1/3 to 1/8<sup>th</sup> the silicon area of a MOSFET for a similar voltage drop at rated current saving space and cost.

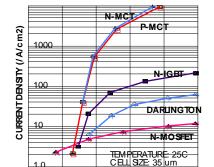
Fast LF-MCTs can be used as a replacement for IGBTs where they have a Vf that is as much as 40% lower than a typical IGBTs.

Although Fast LF-MCTs must be driven with a +/- gate voltage, the small current requirement allows the negative voltage to be generated from the output of a typical switching gate drive. Additionally, a positive or negative pulse will latch them on or off and a continuous voltage is not required.

The LND090 are packaged in lead free TO-252 packages or available as hare die

### PASS ELEMENT CURRENT DENSITY

COMPARISON OF 600V DEVICES WITH LESS THAN 1 us TURN-OFF TIME



0.5 1.0 1.5 FORWARD DROP (VOLTS) **Modelled Forward Drop Comparison** of MOSGated Power Devices

2.0

## **FEATURES**

- 600V/1500V anode to cathode voltage
- Off leakage 30% of equivalent MOSFET
- High impedance MOSFET-like gate
- Vg=+/- 5V gate drive, pulsed OK
- Turn off current:
  - 1A & 3A LF-MCTs (A,B)
  - 10A & 40A LF-MCTs (C,D)
- Low gate capacitance ~ 380pF
- Ultra fast rise times ~ 17ns
- Sub ~200ns fall times
- Silicon area reduced to as little as 30% of the silicon of a MOSFET with equivalent Vf
- Up to 10x the peak current capability of an equivalent MOSFET
- >40% lower forward Vf drop than IGBTs (1.3-1.6V vs. ~2.2V for IGBT)
- High current density >> 300 Amp Peak
- Lead free RoHS compliant TO-252 PKG
- Also available as bare die

# APPLICATIONS

- Crowbar protection circuits
- High-voltage surge suppressors
- Uninterruptible Power Supplies
- Capacitor discharge safety switches
- White Goods, Rice Cookers
- AC/DC Flyback Converters
- DC/DC Switching Applications
- Resonant switching
- Plasma Televisions
- Camera Strobe

### PACKAGE & SYMBOL





